1 Flash-Based SSDs

Vocabularies

1. Flash Solid-State Storage

• Is a type of non-volatile computer storage that stores and retrieves digital information using only electronic circuits, without any involvement of moving mechanical parts

2. NAND-Based Flash

• Is an electronic non-volatile computer memory storage medium using NAND-gate that can be electrically erased and reprogrammed.

3. Flash Page

• Is the smallest unit that can be programmed into flash

4. Flash Block

• Is a group of pages and the smallest unit that can be erased.



5. Wear Out

- Is similar to going past **expiration date**
- Means it has exceeded their endurance rating

6. Single-Level Cell

• Is a type of cell in solid-state storage that stores one bit of data per transister (0 or 1)

7. Multi-Level Cell

• Is a type of cell in solid-state storage that stores two bits of data (i.e 00, 01, 10, 11) per cell using two different levels of charge

8. Triple-Level Cell

• Is a type of cell in solid-state storage that stores three bits of data per cell (i.e 000, 001, 010, 011, 100, 101, 110, 111)

9. Bank / Plane

• Is a group of large number of cells

10. Head Crash

• Is a condition where the drive head makes contact with the recording surface

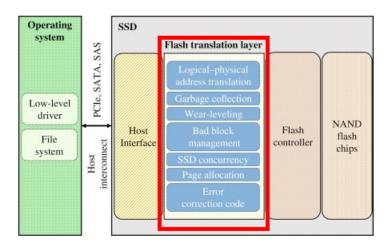


11. Disturbance

- Is also known as read disturbance or program disturbance
- Is a condition where accessing a bit in a page causes some bits to get flipped in neighboring pages

12. Flash Transition Layer

• Is an intermediate system made up software and hardware that manages SSD operations



13. Wear Leveling

• Is a technique for prolonging the service life of some kinds of erasable computer storage media, such as flash memory, which is used in solid-state drives (SSDs)

14. Direct Mapped

• Is a simplest organization of an **Flash Transition Layer** that maps read of logical page N directly to read of playsical page N.

15. Logging

• Is a concept in **log-structured file system** that buffer all writes (data + metadata) using an in-memory segment; once the segment is full, write the segment to a log

16. Logical Block Address

• Is a common scheme used for specifying the location of blocks of data stored on computer storage devices, generally in secondary storage system



17. In-Memory Mapping Table

• Is a table inside the memory of the secondary storage device (is persistent in some form) that stores the physical address of each logical block in the system

18. Garbage Block

- Is also called **Dead Block**
- Is old version of block in secondary storage, such as solid state drive

19. Garbage Collection

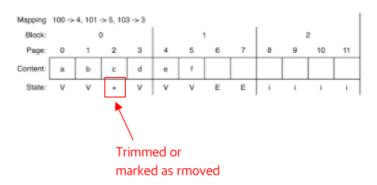
• Is the process of finding garbage blocks and reclaiming them for future use

20. Cache Flush

• Is the process of clearing out sections of memory to ensure writes have actually been persisted in solid state drive

21. **Trim**

• Is an operation that takes an address (and possibly a length) and informs the device that the block(s) specified by the address (and length) have been deleted



22. Overprovision

• Is an extra amount of flash space used to reduce the cost of **garbage collection**, increase the logitivity of flash drive, and prevents the device from slowing down



23. Page-Level FTL

- Is an intermediate system made of software and hardware that manages SSD operations at page-level.
 - It does not write a full block
 - Only writes the necessary page(s) of data along with the FTL metadata that must be written to track of the new position of the data

24. Hybrid Mapping

• Is a mapping technique used in **Flash Transition Layer** that utilizes both block-based mapping and page-based mapping to enable flexible writing but also reduce mapping costs

25. Log Blocks

 Are blocks in solid state storage where contents are erased and all writes are directed

26. Switch Merge

• This will be revisited when reading related section

27. Partial Merge

• This will be revisited when reading related section

28. Full Merge

• This will be revisited when reading related section

1.1 Flash-Based SSDs

- Has two interesting problems to overcome
 - 1. To write a small chunk (called **flash page**), a bigger chunk (**flash block**) must be erased first
 - 2. Writing too often would cause a page to wear out

1.2 Storing a Single Bit

- Single-level cell \rightarrow 1 bit per cell
- Multi-level cell \rightarrow 2 bits per cell
- Triple-level cell \rightarrow 3 bits per cell
- Single-level cell has higher performance and are more expensive
 - More 촘촘하다
- How SLC, MLC, TLC works \rightarrow Physics!!

1.3 From Bits to Banks / Planes

Question Is conent in a flash chip a cell? How many bits can be stored per content?

Question I should ask clarification from professor about why Samsung and other tech giants are producing higher level cells if SLC is better in performance

- In each plane/bank, there are large number of blocks
- In each block, there are a large number of pages



1.4 Basic Flash Operations

- Read (a page):
 - Is fast ($10 \mu s$)
 - Can access any location uniformly
 - * flash-based SSD is a random access device
- Erase (a block):
 - Is most expensive
 - block must be erased before erasing a page



• Program (a page):

- Is used to change some of the 1's within a page to 0's and vice versa
- Is less expensive then erasing a block
- Is more costly than reading a page
- Before overwriting any page within a block, we must first move any data we care about to another location
 - * Frequent repeatitions of program/erase cycle cause flash chips to wear out
- Page starts in INVALID state
- Erasing block results in pages with ERASED state
 - resets contents in page
 - makes contents re-programmable
- Programming a page results in VALID state
 - Contents are set and can be read
 - Only way to change it's content is to erase the entire block

```
iiii
                             Initial: pages in block are invalid (i)
Erase()
                    EEEE
                             State of pages in block set to erased (E)
Program(0)
                            Program page 0; state set to valid (V)
                    VEEE
Program(0)
                    error
                             Cannot re-program page after programming
Program(1)
                    VVEE
                            Program page 1
                    EEEE
                             Contents erased; all pages programmable
```

1.5 Flash Performance and Reliability

• Performance

		Read	Program	Erase	Slower
	Device	(μs)	(μs)	(μs)	as more bits
Single-layer cell ———	→ SLC	25	200-300	1500-2000	packed per
Multi-layer cell ———	MLC	50	600-900	~3000	packed per
Triple-layer cell ———	→ TLC	~75	~900-1350	~4500	▼ cell

• Reliability Concerns

- Wear Out

- * Accures a bit of extra charge when flash block is erased and programmed
- * Over time, 0 and 1 become difficult to distinguish
- * Becomes unusable at the point where it becomes impossible to distinguish

- Disturbance

- * Access a page within a flash may cause some bits to get flipped in neighboring pages
- * Disturbance while programming \rightarrow Program Disturbance
- * Disturbance while reading \rightarrow Read Disturbance

1.6 From Raw Flash to Flash-Based SSDs

- Addresses the question "How to turn a basic set of flash chips into something that looks like a typical storage device"
- Hardware Requirements
 - Flash chips
 - Some volatile memory for caching (e.g. SRAM)
 - Control logic to orchestrate device operation

• Other Requirements

Flash Transition Layer

- * Is made up of both hardware and software
- * Takes read and write requests on logical blocks
- * Turns contents in logical blocks into low-level read, erase, and program commands on the underlying $physical\ page$ and $physical\ block$
- * FTL should accomplish this task with the goal of excellent performance and high reliability

- 1.7 FTL Organization: A Bad Approach
- 1.8 A Log Structured FTL
- 1.9 Garbage Collection
- 1.10 Mapping Table Size
- 1.11 Hybrid Mapping
- 1.12 Wear Leveling
- 1.13 SSD Performance And Cost